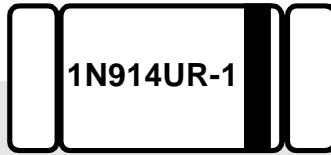


MINI-MELF-SMD



Silicon Switching Diode

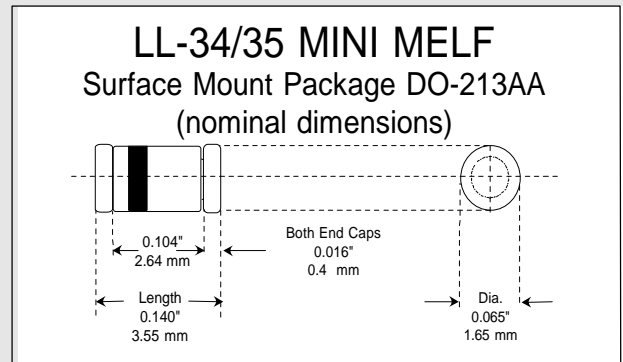
Applications

Used in general purpose applications, where performance, space and switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability
- Also comes in DO-35 glass package
- Full UR approval to Mil-S-19500/116
- Available up to JANTXV levels
- "S" level screening available to Source Control Drawings

1N914UR-1 / LL914



Maximum Ratings	Symbol	Value	Unit
Peak Inverse Voltage	PIV	100 (Min.)	Volts
Average Rectified Current	I_{Avg}	200	mAmps
Continuous Forward Current	I_{Fdc}	300	mAmps
Peak Surge Current ($t_{peak} = 1 \text{ sec.}$)	I_{peak}	1.0	Amp
BKC Power Dissipation @ end cap $T = 50 \text{ }^\circ\text{C}$	P_{tot}	500	mWatts
Storage & Operating Temperature Range	$T_{St \& Op}$	-65 to +200	$^\circ\text{C}$

Electrical Characteristics @ 25°C	Symbol	Maximum Limits	Unit
Forward Voltage Drop @ $I_F = 10 \text{ mA}$	V_F	1.0	Volts
Forward Voltage Drop @ $I_F = 100 \text{ mA}$	V_F	1.2	Volts
Reverse Leakage Current @ $V_R = 20 \text{ V}$	I_R	0.025 (50 @ 150 °C)	μA
Reverse Leakage Current @ $V_R = 75 \text{ V}$	I_R	0.50 (100 @ 150 °C)	μA
Capacitance @ $V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$	C_T	4.0	pF
Capacitance @ $V_R = 1.5 \text{ V}$, $f = 1 \text{ MHz}$	C_T	2.8	pF
Reverse Recovery Time (note 1)	t_{rr}	5.0	nSecs
Forward Recovery Time (note 2)	V_{fr}	20	nSecs

Note 1: $I_F = I_R = 10 \text{ mA}$, $R_L = 100 \text{ Ohms}$ Note 2: $I_F = 50 \text{ mA dc}$

To order MIL parts, use the 1N914UR-1 number with the appropriate JAN, JTX or JTXV prefix.

1N914-1 DO-35 glass leaded parts also available in both commercial and military versions.